preliminary

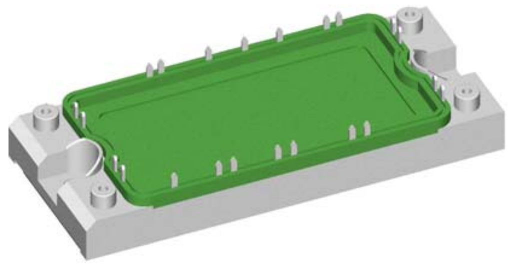
High Voltage Thyristor Module

3~ Rectifier				Brake Chopper			
V_{RRM}	=	2200	V	V_{CES}	=	1700	V
I_{DAV}	=	117	A	I_{C25}	=	113	A
I_{FSM}	=	500	A	$V_{CE(sat)}$	=	2.5	V

3~ Rectifier Bridge, half-controlled (high-side) + Brake Unit

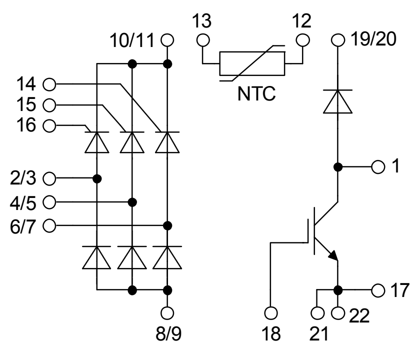
Part number

MCNA120UI2200TED



Backside: isolated

E72873



Features / Advantages:

- Thyristor/Standard Rectifier for line frequency
- Planar passivated chips
- Long-term stability
- Low forward voltage drop
- Leads suitable for PC board soldering
- Copper base plate with Direct Copper Bonded Al2O3-ceramic
- Improved temperature and power cycling

Applications:

- Drive Inverters with brake system

Package:

- Housing: E2-Pack
- International standard package
- RoHS compliant
- Isolation voltage: 3600 V~
- Advanced power cycling

IXYS reserves the right to change limits, conditions and dimensions. Data according to IEC 60747and per diode unless otherwise specified 20120307a

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Thyristor

Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			2300	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			2200	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 2200 V	T_{VJ} = 25°C			50	µA
		$V_{R/D}$ = 2200 V	T_{VJ} = 125°C			10	mA
V_T	*forward voltage drop*	I_T = 40 A	T_{VJ} = 25°C			1.33	V
		I_T = 80 A				1.70	V
		I_T = 40 A	T_{VJ} = 125°C			1.36	V
		I_T = 80 A				1.88	V
I_{DAV}	*bridge output current*	T_C = 80°C	T_{VJ} = 150°C			117	A
		rectangular d = ⅓					
V_{T0}	*threshold voltage*	*for power loss calculation only*	T_{VJ} = 150°C			0.83	V
r_T	*slope resistance*					13.6	mΩ
R_{thJC}	*thermal resistance junction to case*					0.65	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			190	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			500	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			540	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			425	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			460	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.25	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.22	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			905	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			880	A²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		18		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 150°C; f = 50 Hz	repetitive, I_T = 120 A			150	A/µs
		t_P = 200 µs; di_G/dt = 0.45 A/µs					
		I_G = 0.45 A; V_D = ⅔ V_{DRM}	non-repet., I_T = 40 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150 °C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25 °C			1.4	V
			T_{VJ} = -40 °C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25 °C			70	mA
			T_{VJ} = -40 °C			150	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150 °C			0.2	V
I_{GD}	*gate non-trigger current*					5	mA
I_L	*latching current*	t_p = 10 µs	T_{VJ} = 25 °C			150	mA
		I_G = 0.45 A; di_G/dt = 0.45 A/µs					
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25 °C			100	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}	T_{VJ} = 25 °C			2	µs
		I_G = 0.45 A; di_G/dt = 0.45 A/µs					
t_q	*turn-off time*	V_R = 100 V; I_T = 40 A; V_D = ⅔ V_{DRM}	T_{VJ} = 150 °C		500		µs
		di/dt = 10 A/µs; dv/dt = 20 V/µs; t_p = 200 µs					

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Brake IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1700	V
V_{GES}	*max. DC gate voltage*					±20	V
V_{GEM}	*max. transient collector gate voltage*					±30	V
I_{C25}	*collector current*		T_C = 25°C			113	A
I_{C80}			T_C = 80°C			80	A
P_{tot}	*total power dissipation*		T_C = 25°C			445	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 75 A; V_{GE} = 15 V	T_{VJ} = 25°C		2.5	2.93	V
			T_{VJ} = 125°C		3		V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 3 mA; V_{GE} = V_{CE}	T_{VJ} = 25°C	5.2	5.8	6.4	V
I_{CES}	*collector emitter leakage current*	V_{CE} = V_{CES}; V_{GE} = 0 V	T_{VJ} = 25°C			0.6	mA
			T_{VJ} = 125°C		5		mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V				400	nA
$Q_{G(on)}$	*total gate charge*	V_{CE} = 900 V; V_{GE} = 15 V; I_C = 75 A			850		nC
$t_{d(on)}$	*turn-on delay time*	inductive load V_{CE} = 900 V; I_C = 75 A V_{GE} = ±15 V; R_G = 18 Ω	T_{VJ} = 125°C		220		ns
t_r	*current rise time*				100		ns
$t_{d(off)}$	*turn-off delay time*				880		ns
t_f	*current fall time*				200		ns
E_{on}	*turn-on energy per pulse*				30		mJ
E_{off}	*turn-off energy per pulse*				25		mJ
RBSOA	*reverse bias safe operating area*	V_{GE} = ±15 V; R_G = 18 Ω	T_{VJ} = 125°C				
I_{CM}		V_{CEK} = 1700 V				150	A
SCSOA	*short circuit safe operating area*						
t_{SC}	*short circuit duration*	V_{CE} = 720 V; V_{GE} = ±15 V	T_{VJ} = 125°C			10	µs
I_{SC}	*short circuit current*	R_G = 18 Ω; non-repetitive			tbd		A
R_{thJC}	*thermal resistance junction to case*					0.28	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W

Brake Diode							
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			1700	V
I_{F25}	*forward current*		T_C = 25°C			75	A
I_{F80}			T_C = 80°C			50	A
V_F	*forward voltage*	I_F = 60 A	T_{VJ} = 25°C			2.45	V
			T_{VJ} = 125°C			2.60	V
I_R	*reverse current*	V_R = V_{RRM}	T_{VJ} = 25°C			0.1	mA
			T_{VJ} = 125°C			1	mA
Q_{rr}	*reverse recovery charge*	V_R = 900 V $-di_F/dt$ = 750 A/µs I_F = 60 A	T_{VJ} = 125°C		15		µC
I_{RM}	*max. reverse recovery current*				60		A
t_{rr}	*reverse recovery time*				550		ns
E_{rec}	*reverse recovery energy*				10		mJ
R_{thJC}	*thermal resistance junction to case*					0.65	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W

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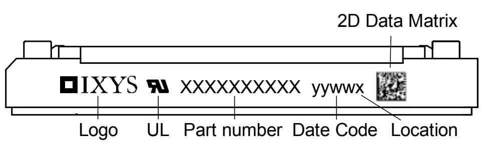
Package E2-Pack

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal			200	A
T_{stg}	*storage temperature*		-40		125	°C
T_{VJ}	*virtual junction temperature*		-40		150	°C
Weight				176		g
M_D	*mounting torque*		3		6	Nm
V_{ISOL}	*isolation voltage*	t = 1 second	3600			V
		t = 1 minute	3000			V
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*	*terminal to terminal*	6.0			mm
$d_{Spb/Apb}$		*terminal to backside*	12.0			mm



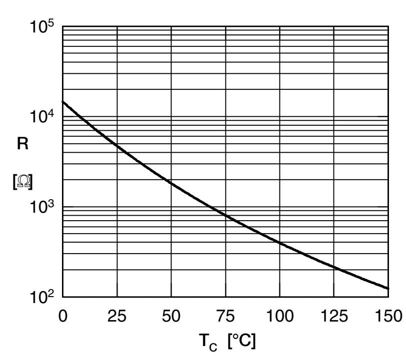
Part number

- M = Module
- C = Thyristor (SCR)
- N = High Voltage Thyristor
- A = (≥ 2000 V)
- 120 = Current Rating [A]
- UI = 3~ Rectifier Bridge, half-controlled (high-side) + Brake Unit
- 2200 = Reverse Voltage [V]
- T = Thermistor \ Temperature sensor
- ED = E2-Pack

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCNA120UI2200TED	MCNA120UI2200TED	Box	6	510374

Temperature Sensor NTC

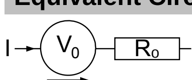
Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	*resistance*	T_{VJ} = 25°	4.75	5	5.25	kΩ
$B_{25/50}$	*temperature coefficient*			3375		K



Typ. NTC resistance vs. temperature

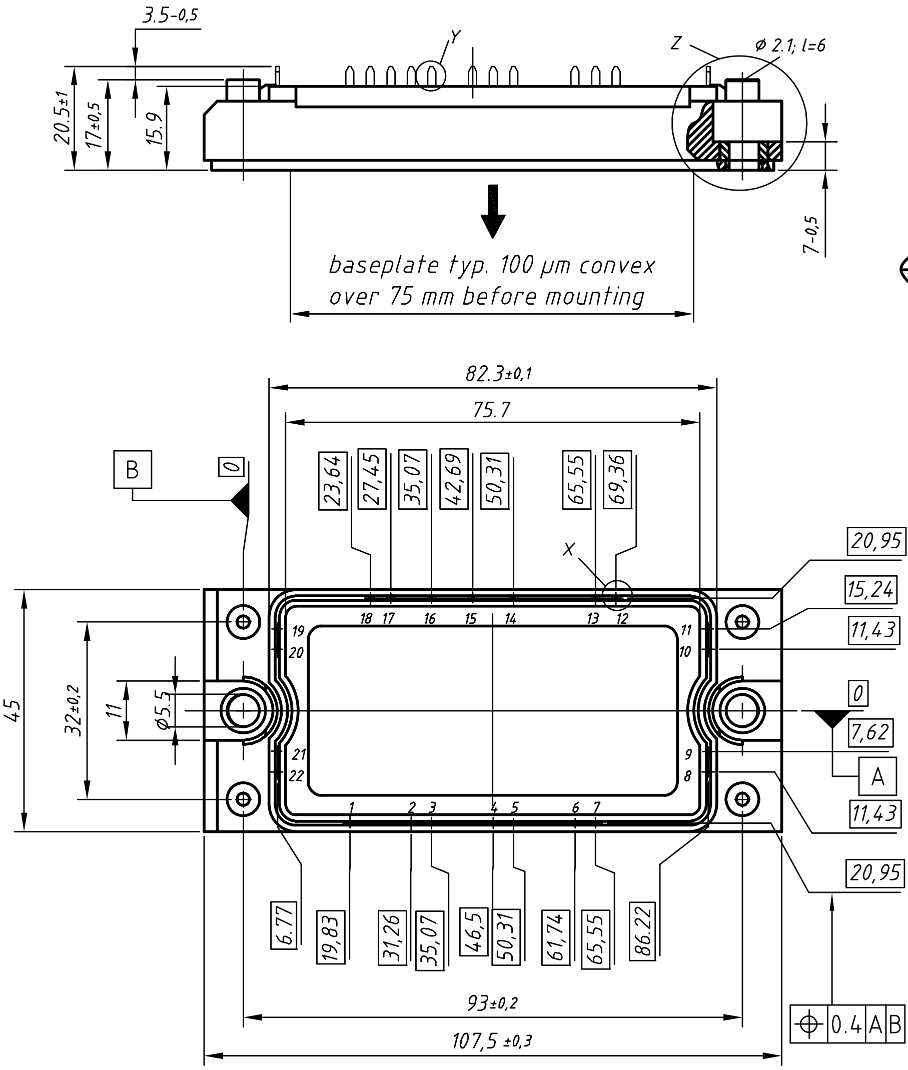
Equivalent Circuits for Simulation

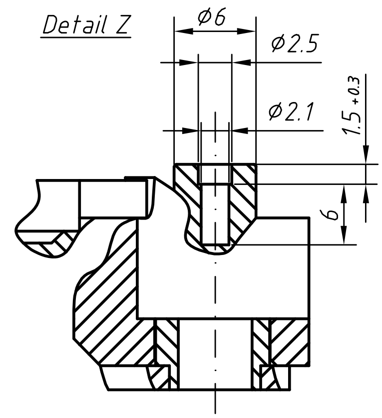
* on die level T_{VJ} = 150°C

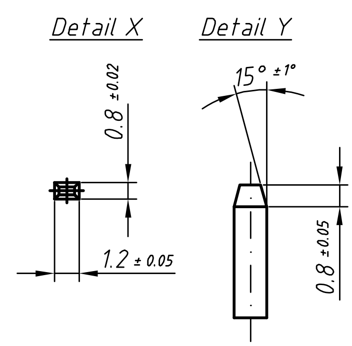


		Thyristor	Brake IGBT	Brake Diode	
$V_{0\,max}$	*threshold voltage*	0.83	1.17	1.34	V
$R_{0\,max}$	*slope resistance **	10.5	25	15.2	mΩ

Outlines E2-Pack







Dimmensions w/o tolerances acc. DIN ISO 2768-T1-m